



CHENMKO ENTERPRISE CO., LTD

SURFACE MOUNT

CHEMF20PT

Lead free devices Power Management (Dual Transistor)

Tr1: VOLTAGE 50 Volts CURRENT 150 mAmpere
DTr2: VOLTAGE 50 Volts CURRENT 30 mAmpere

APPLICATION

- * Power management circuit

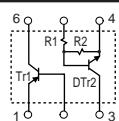
FEATURE

- * Small surface mounting type. (SOT-563)
- * Power switching circuit in a single package.
- * Mounting cost and area can be cut in half.
- * Both the 2SC4617 & CHDTC144E in one package.
- * Built in bias resistor(R1=47kΩ, Typ.)

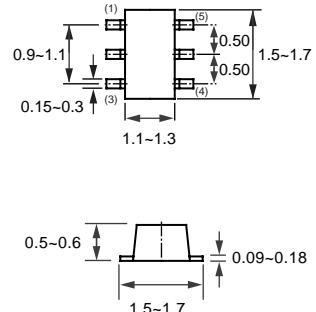
MARKING

- * FD

CIRCUIT



SOT-563



Dimensions in millimeters

SOT-563

2SC4617 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	Collector-base voltage		—	60	V
V _{CEO}	Collector-emitter voltage		—	50	V
V _{EBO}	Emitter-base voltage		—	7	V
I _C	DC Output current		—	150	mA
P _C	Total power dissipation	NOTE.1	—	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		—	150	°C

Note

1. 120mW per element must not be exceeded.

2004-07

CHDTC144E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Vcc	Supply voltage		–	50	V
VIN	Input voltage		-10	+40	V
Io	DC Output current IC(Max.)		–	30	mA
		NOTE.1	–	100	
Pc	Power dissipation	NOTE.2	–	150	mW
TSTG	Storage temperature		-55	+150	°C
TJ	Junction temperature		–	150	°C

Note

1. Characteristics of built-in transistor.
2. Each terminal mounter on a recommended land.

2SC4617 CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCEO	Collector-emitter breakdown voltage	Ic=50uA	60	–	–	V
BVcbo	Collector-base breakdown voltage	Ic=1mA	50	–	–	V
BVEBO	Emitter-base breakdown voltage	Ie=50uA	7	–	–	V
Icbo	Collector cut-off current	Vcb=60V	–	–	100	nA
Ieb0	Emitter cut-off current	Veb=7V	–	–	100	nA
hFE	DC current gain	Vce=6V, Ic=1mA	120	–	560	–
Vce(sat)	Collector-emitter saturation voltage	Ic=50mA, Ib=5mA	–	–	0.4	V
Cob	Collector output capacitance	Vcb=12V, Ie=0mA, f=1MHz	–	2	3.5	pF
fT	Transition frequency	Vce=12V, Ie=-2mA, f=100MHz	–	180	–	MHz

Note

1. Pulse test: tp≤300uS; δ≤0.02.

CHDTC144E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Vloff	Input off voltage	Io=100uA; Vcc=5.0V	0.5	–	–	V
VI(on)	Input on voltage	Io=2mA; Vo=0.3V	–	–	3.0	V
VO(on)	Output voltage	Io=10mA; II=0.5mA	–	0.1	0.3	V
II	Input current	VI=5V	–	–	180	uA
IC(off)	Output current	VI=0V; Vcc=50V	–	–	500	nA
G1	DC current gain	Io=5mA; Vo=5.0V	20	–	–	–
R1	Input resistor		32.9	47	61.1	KΩ
R2/R1	Resistor ratio		0.8	1.0	1.2	–
fT	Transition frequency	Ie=-5mA, Vce=10.0V f=100MHz	–	250	–	MHz

Note

- Pulse test: tp≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHEMF20PT)

2SC4617 Typical Electrical Characteristics

Fig.1 Grounded emitter propagation characteristics

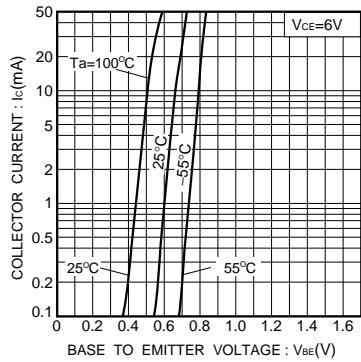


Fig.2 Grounded emitter output characteristics (1)

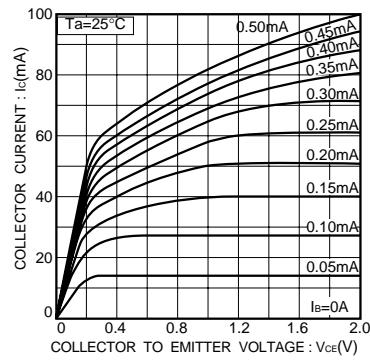


Fig.3 Grounded emitter output characteristics (2)

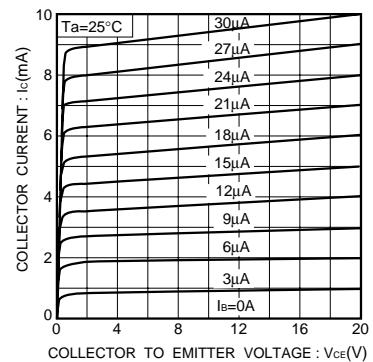


Fig.4 Collector-emitter saturation voltage vs. collector current

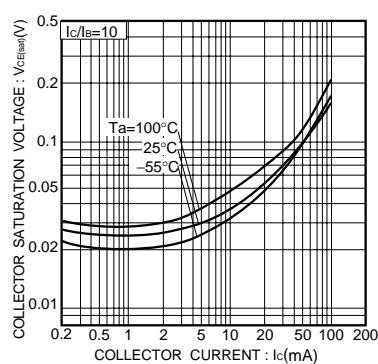


Fig.5 DC current gain vs. collector current

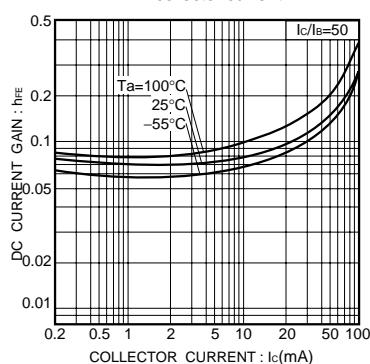
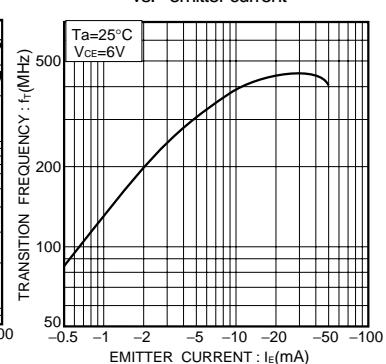


Fig.6 Gain bandwidth product vs. emitter current



RATING CHARACTERISTIC CURVES (CHEMF20PT)

CHDTC144E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current
(ON characteristics)

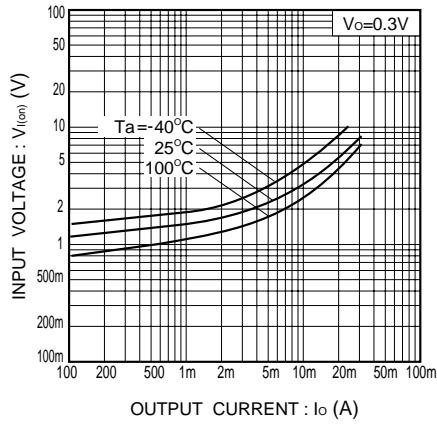


Fig.2 Output current vs. input voltage
(OFF characteristics)

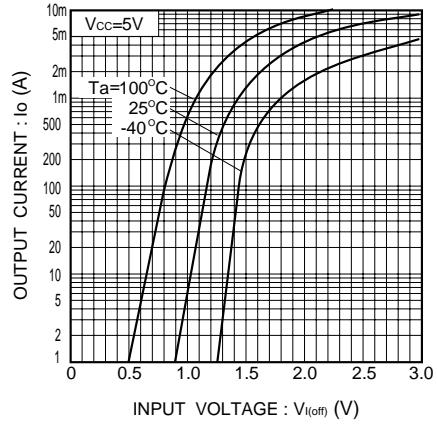


Fig.3 DC current gain vs. output current

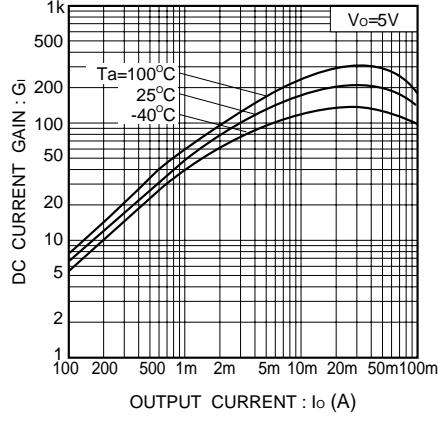


Fig.4 Output voltage vs. output current

